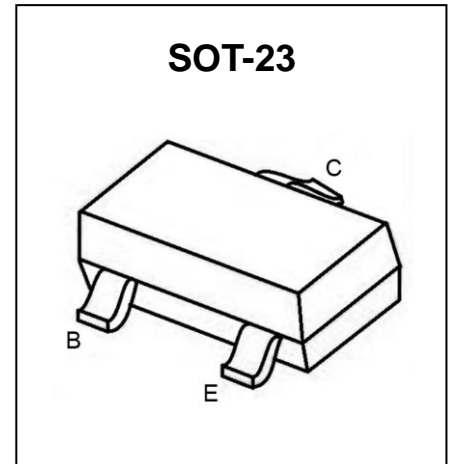




**SS8550 Transistor(PNP)**

**Feature**

- PNP epitaxial silicon , planar design
- Collector-emitter voltage  $V_{CE}=-25V$
- Collector current  $I_C=-1.5A$
- In compliance with ER RoHS 2002/95/EC directives
- Transition frequency  $f_T >100MHz@I_C=-50mA$ ,  
 $V_{CE}=-10Vdc, F=30MHz$



**MAXIMUM RATINGS ( $T_a=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-1.5	A
Power Dissipation	$P_d$	0.3	W
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}C$

**MARKING:**



**Classification of hfe:**

RANK	L	H	J
RANGE	120~200	200~350	350~400

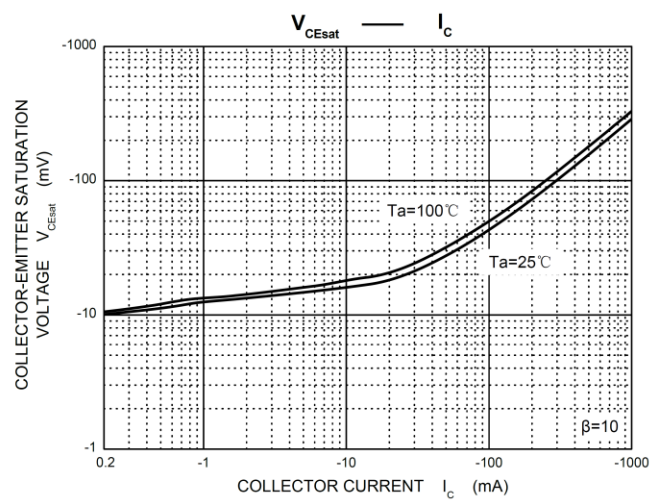
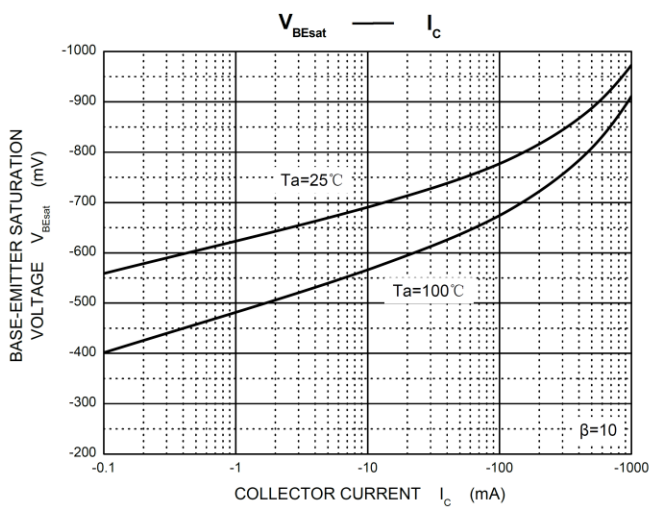
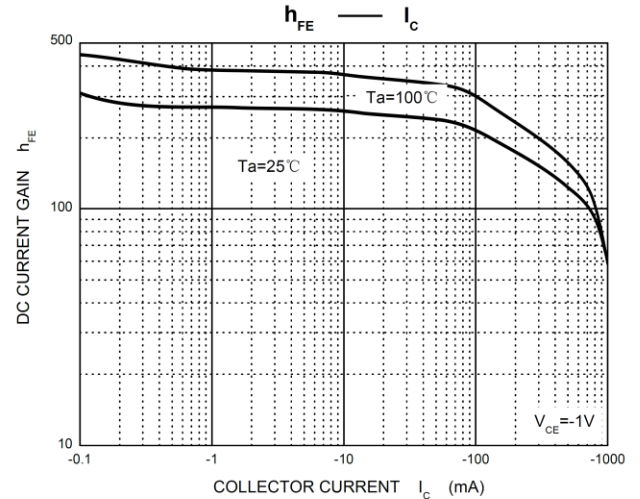
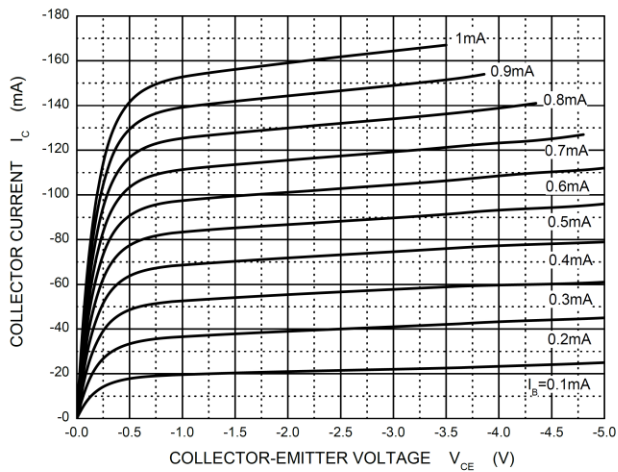
**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

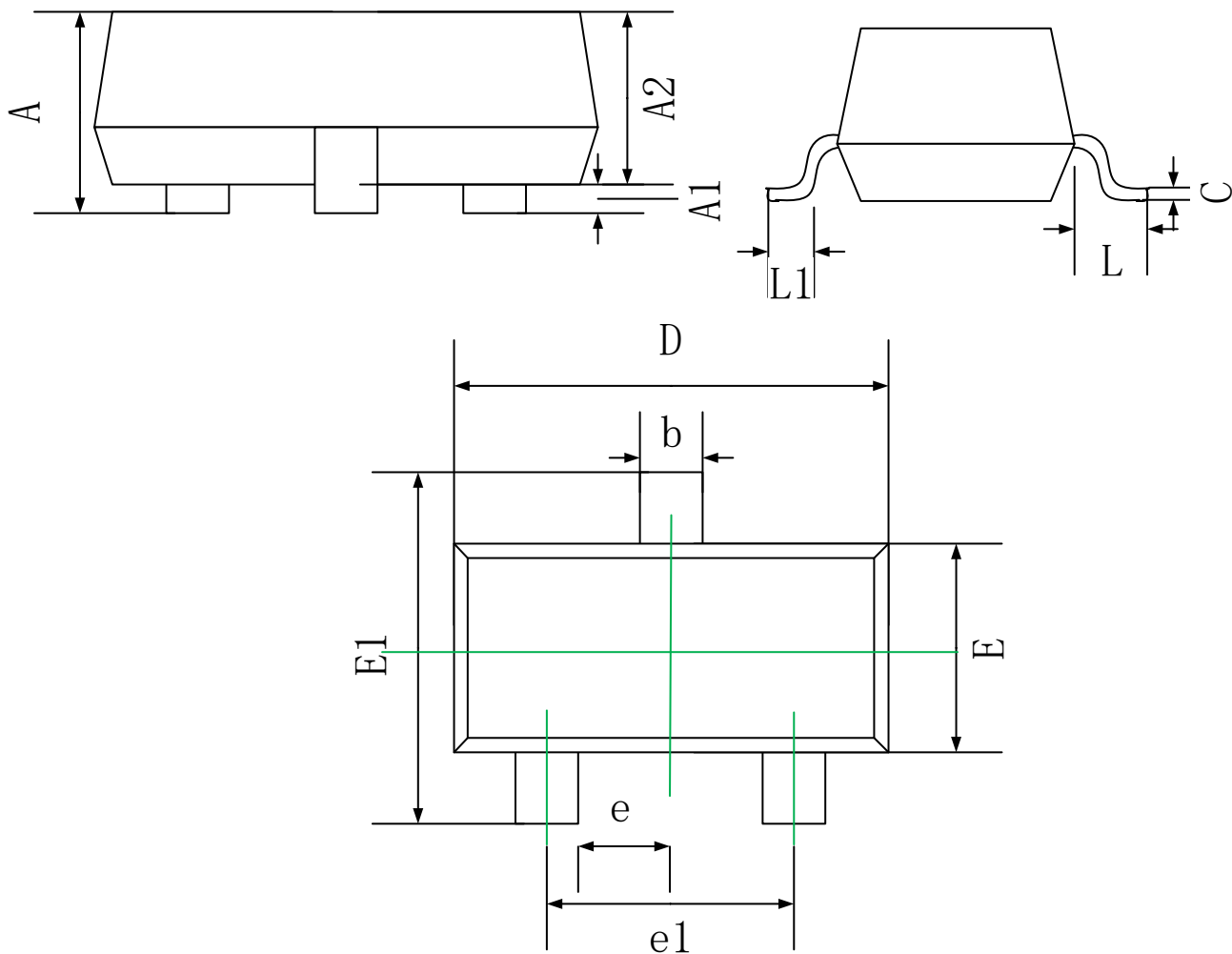
Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-25		V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0		-100	nA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-20V, I <sub>B</sub> =0		-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0		-100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-0.1mA	40		
	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-1mA	70		
	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	100	400	
	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-400mA	60		
	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-800mA	30		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA		-0.5	V
		I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA		-0.6	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA		-1.1	V
		I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA, f=30MHz	100		MHZ
Input capacitance	C <sub>IB</sub>	V <sub>CB</sub> =-5V, I <sub>E</sub> =0, f=1MHz		4	pF
Output capacitance	C <sub>OB</sub>	V <sub>EB</sub> =-0.5V, I <sub>C</sub> =0, f=1MHz		8	pF
Delay time	t <sub>d</sub>	V <sub>CC</sub> =-3V, V <sub>BE</sub> =0.5V,		35	nS
Rise time	t <sub>r</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA		35	nS
Storage time	t <sub>s</sub>	V <sub>CC</sub> =-3V, V <sub>BE</sub> =0.5V,		200	nS
Fall time	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> =-1mA		50	nS

\*Pulse Test: Pulse Width<300uS , Duty Cycle<2.0%

Typical Characteristics

Static Characteristic



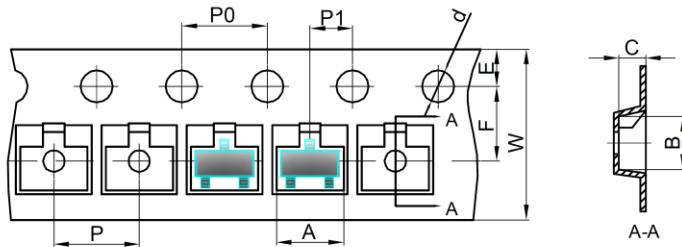
**SOT-23 Package Information**


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

**SOT-23 Tape and Reel**

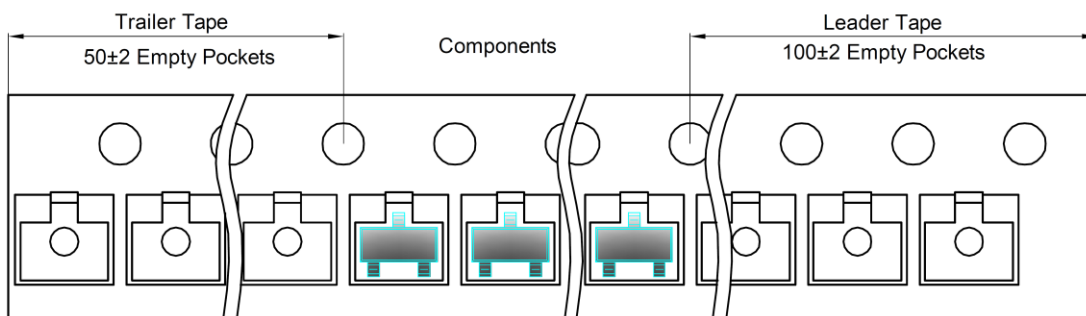
# SOT-23 Tape and reel

## SOT-23 Embossed Carrier Tape

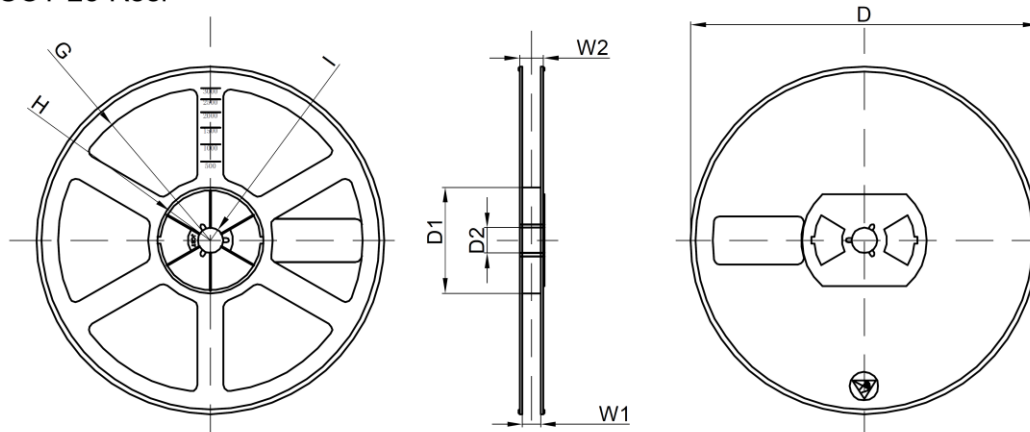


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

## SOT-23 Tape Leader and Trailer



## SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)